

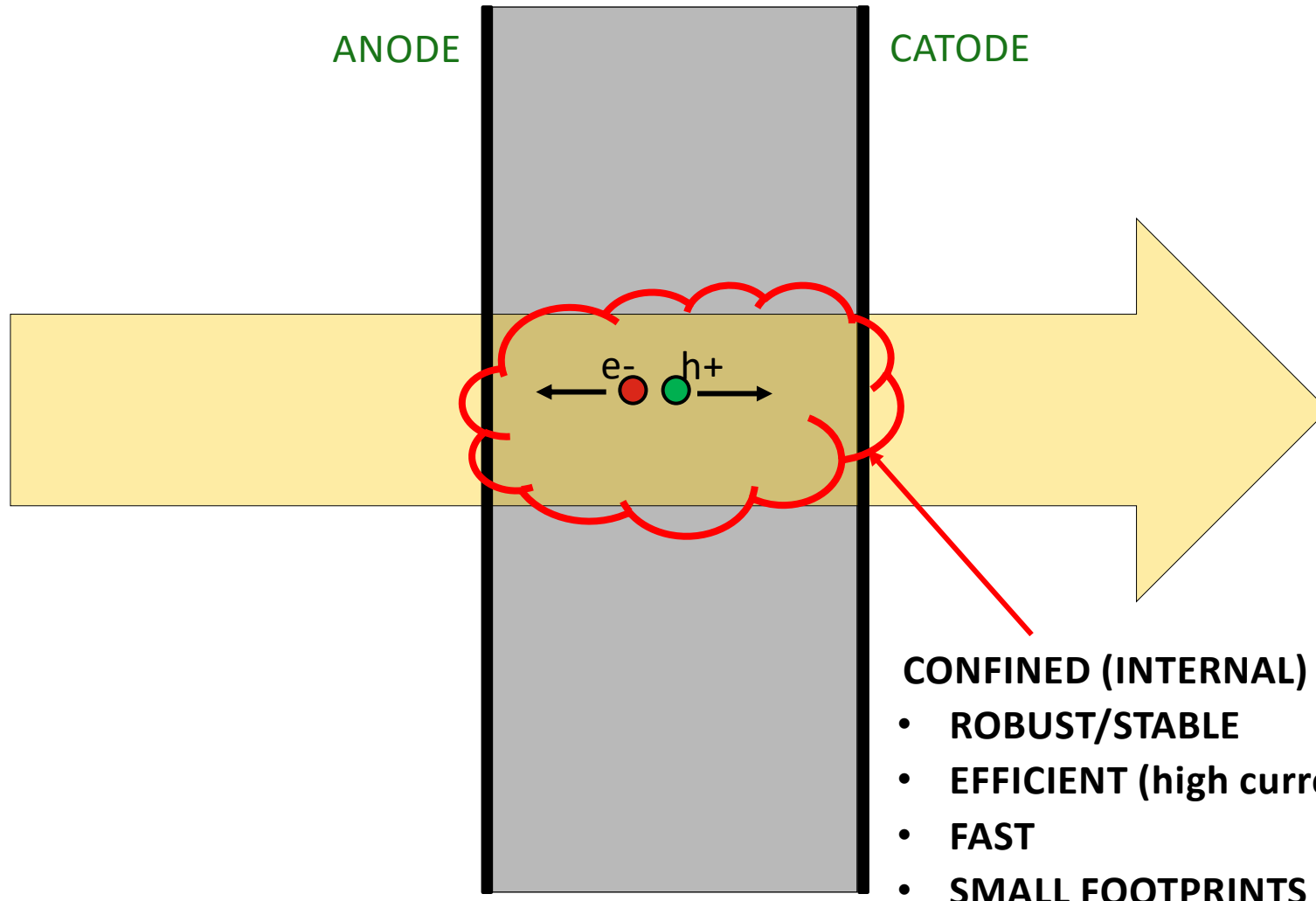


Photon Meadow conference

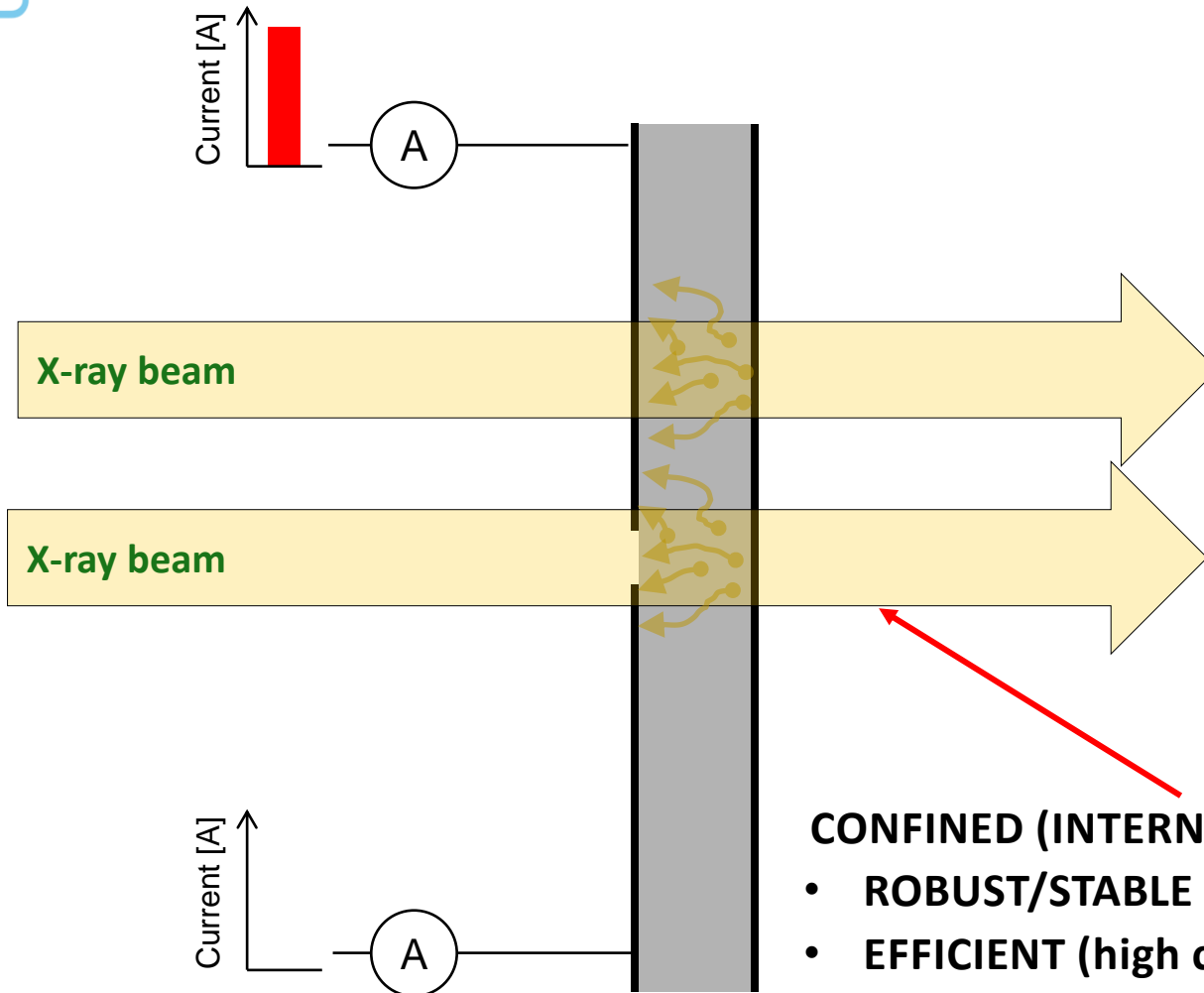
Camarda Massimo, SenSiC GmbH

“Silicon Carbide ultra-thin membranes for X-ray beam position and intensity monitoring”

- Consideration on solid-state sensors for inline photon diagnostic
- Comparisons on solid state sensors materials
- Opportunities offered by Silicon Carbide membranes
- Achievements (for synchrotron beams)
- Results on “First light” at the Swiss Free Electron Laser
- Conclusions



Considerations on solid-state sensors for inline photon diagnostics

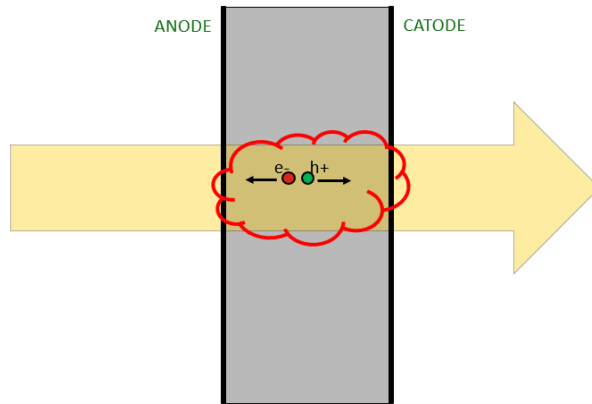


CONFINED (INTERNAL) GENERATION

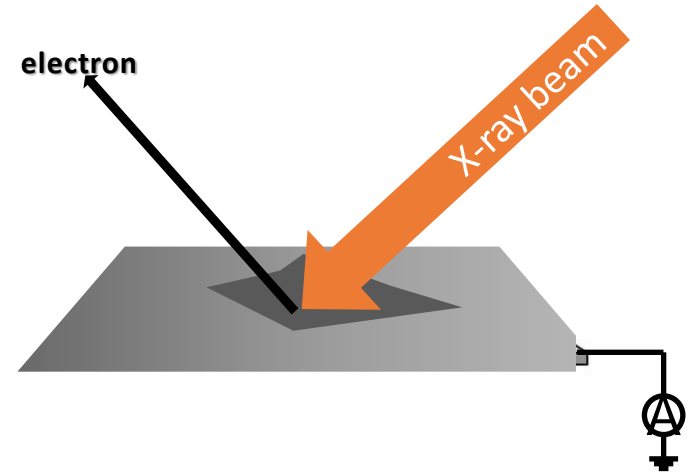
- ROBUST/STABLE
- EFFICIENT (high currents)
- FAST
- SMALL FOOTPRINTS
- **HIGH LATERAL RESOLUTIONS**

Comparison of X-ray sensors

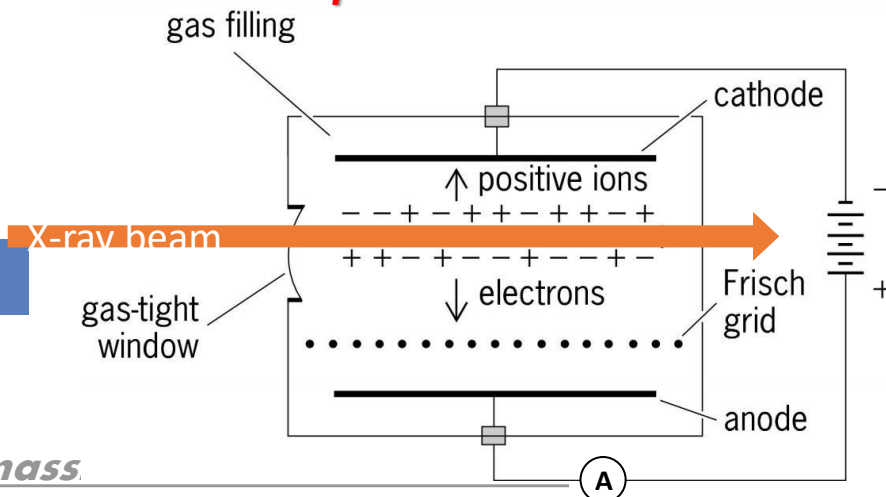
**solid-state based
internal photoemission**



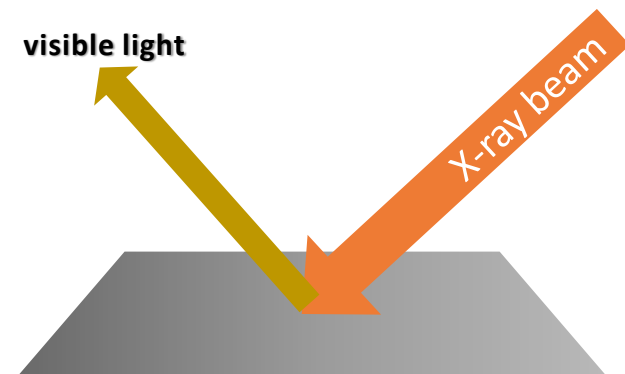
**metal based
external photoemission**



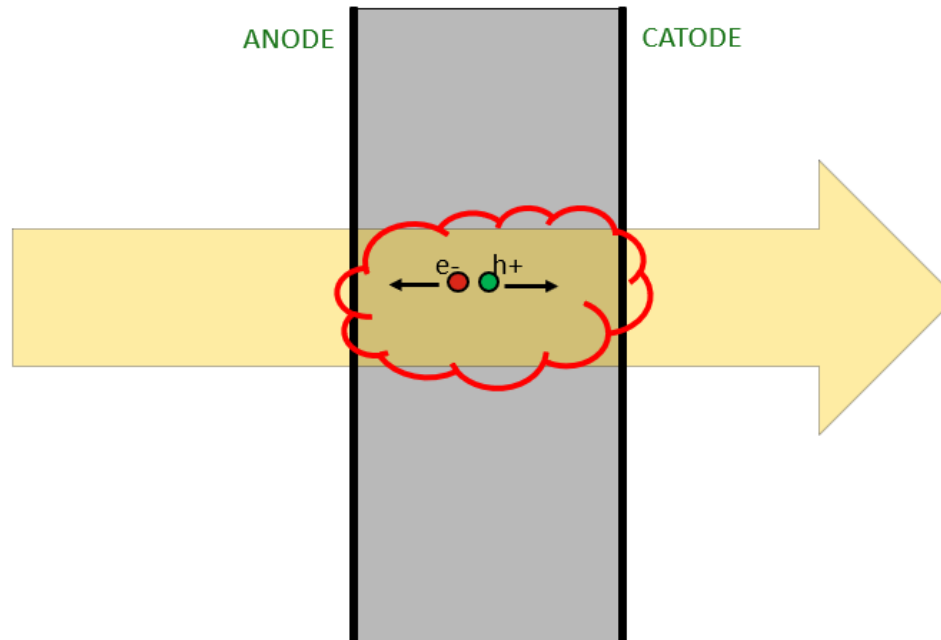
**gas based
photoionization**



fluorescence screen



Considerations on solid-state sensors for photon diagnostics



- CRITICAL ASPECTS** {
- transparency (>98%)
 - stability over time (device degradation)

Best possible material for solid-state sensors

DIAMOND (CARBON)



Property	Diamond
melting point	4500°C
Thermal conductivity	>1500W/m/K
Xray transparency	high

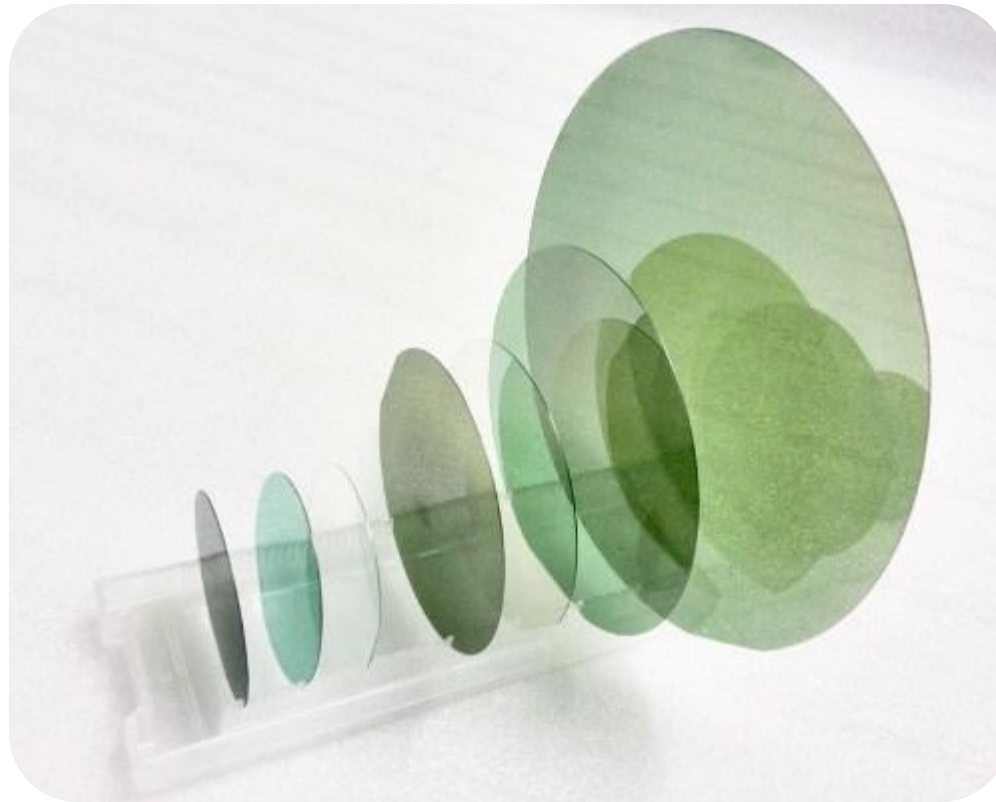
DIAMOND (CARBON)



Property	Diamond
material costs	very high
Available crystal size	0.25cm ² (5mmx5mm)
Quality of crystals	“optical” grade
Electron/Hole generation energy	13eV
Doping control	minimal (>1E20cm ⁻³)

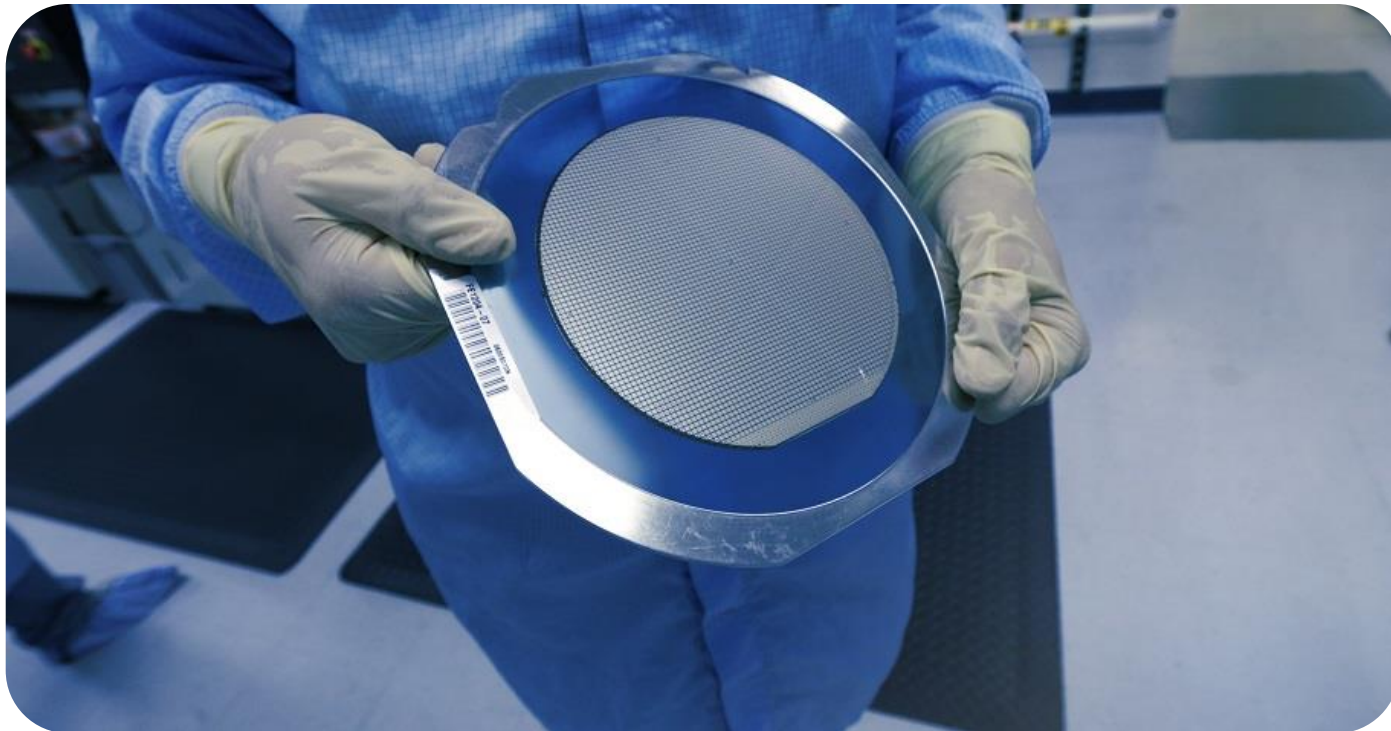
Best possible material for solid-state sensors

SILICON CARBIDE



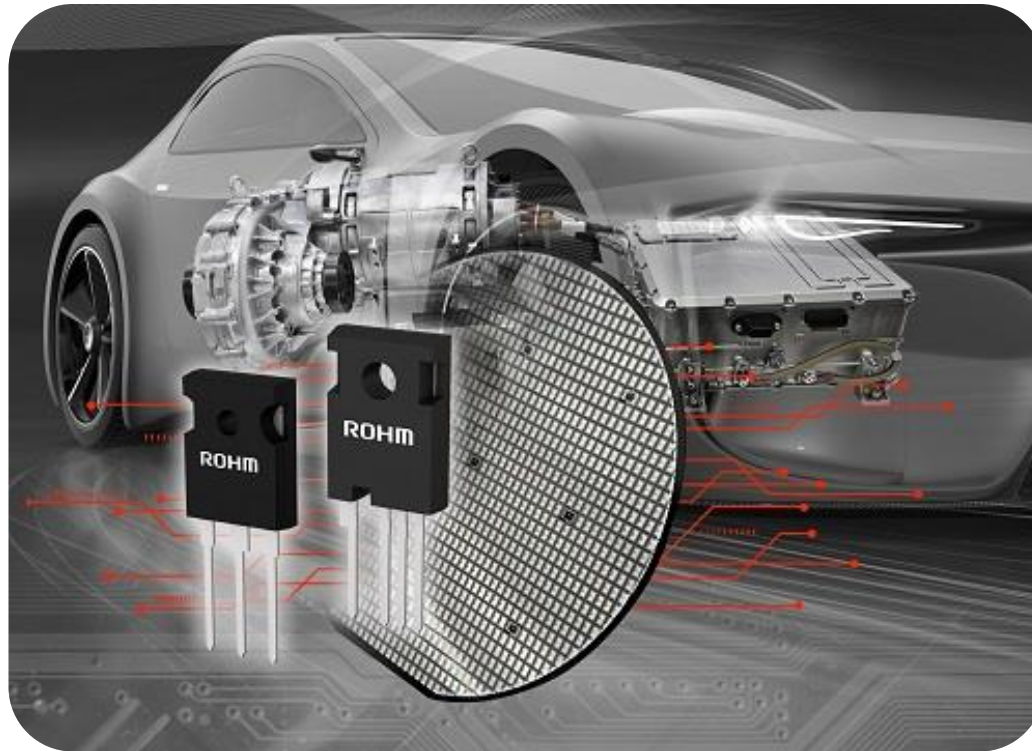
Best possible material for solid-state sensors

SILICON CARBIDE



Best possible material for solid-state sensors

SILICON CARBIDE



Best possible material for solid-state sensors

Property	Diamond	Silicon Carbide
melting point	4500°C	2700°C
Thermal conductivity	>1500W/m/K	400W/m/K
material costs	very high	medium/low
Available crystal size	0.25cm ² (5mmx5mm)	315cm ² (8inch)
Quality of crystals	“optical/electrical” grade	fully industrial
Electron/Hole generation energy	13eV	7.8eV
Doping control	minimal (>1E20cm ⁻³)	high (>5E13cm ⁻³)
Stability of metallisations	low	high

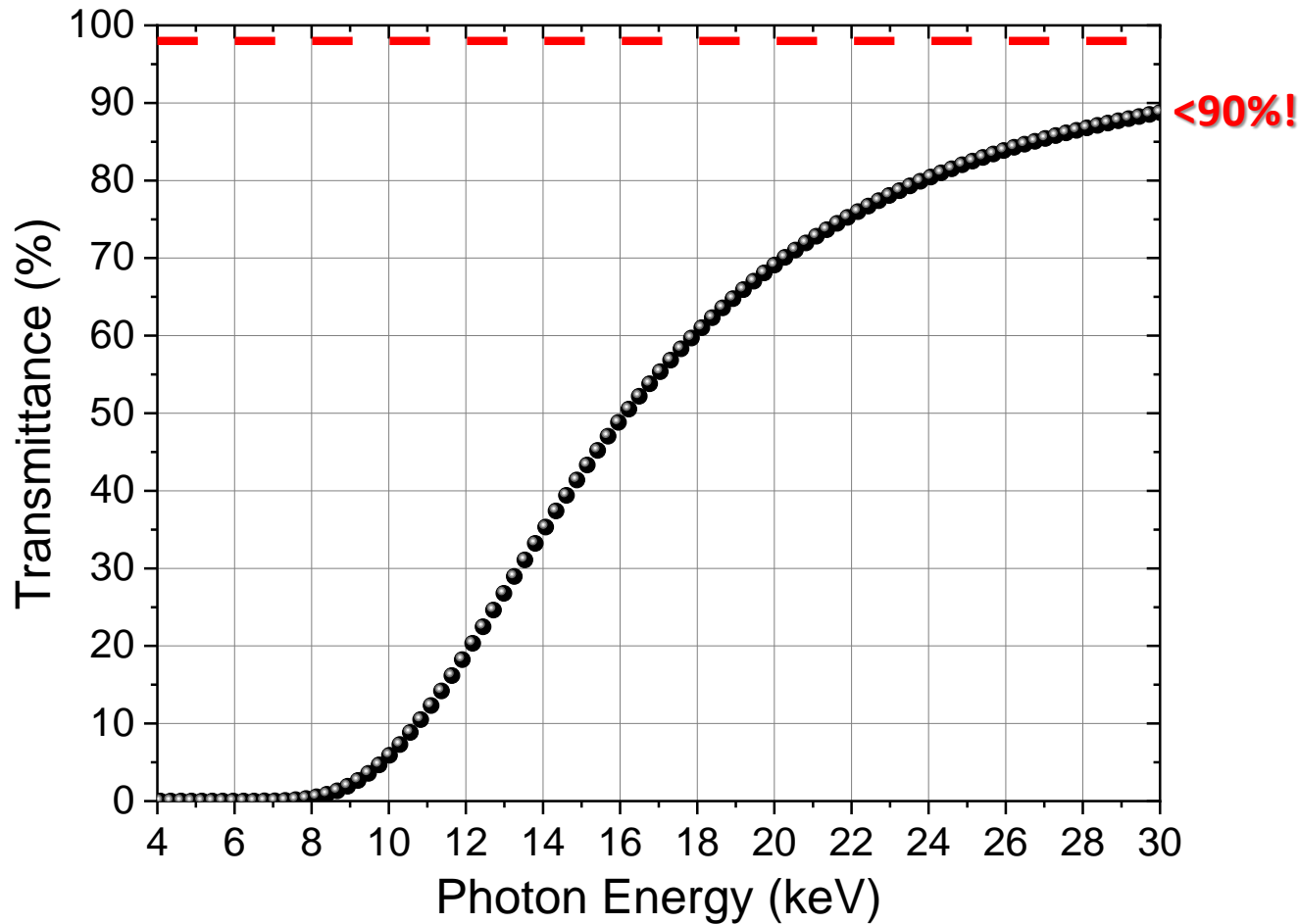
x1260!

Higher signal

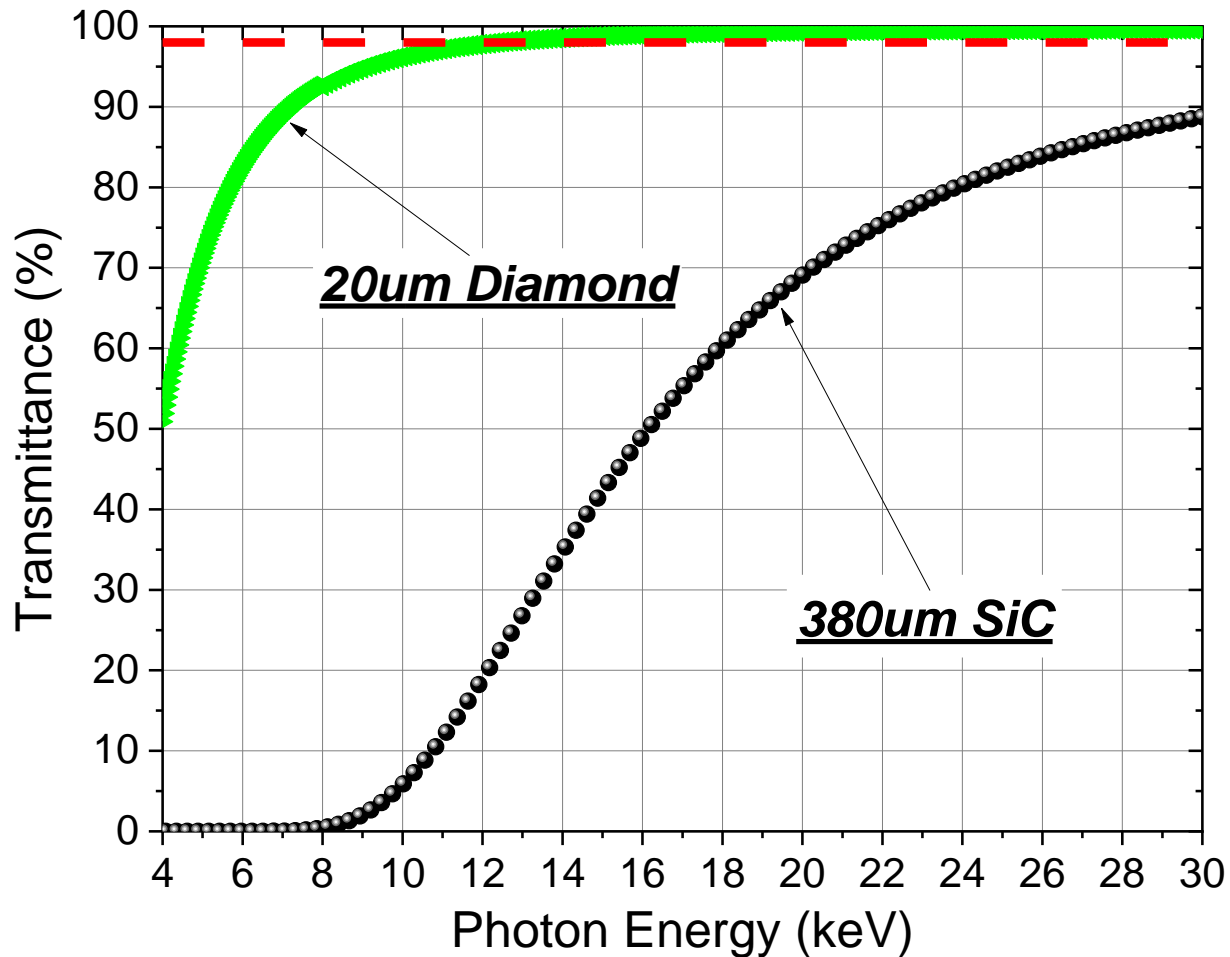
Better sensitivity

Better reliability

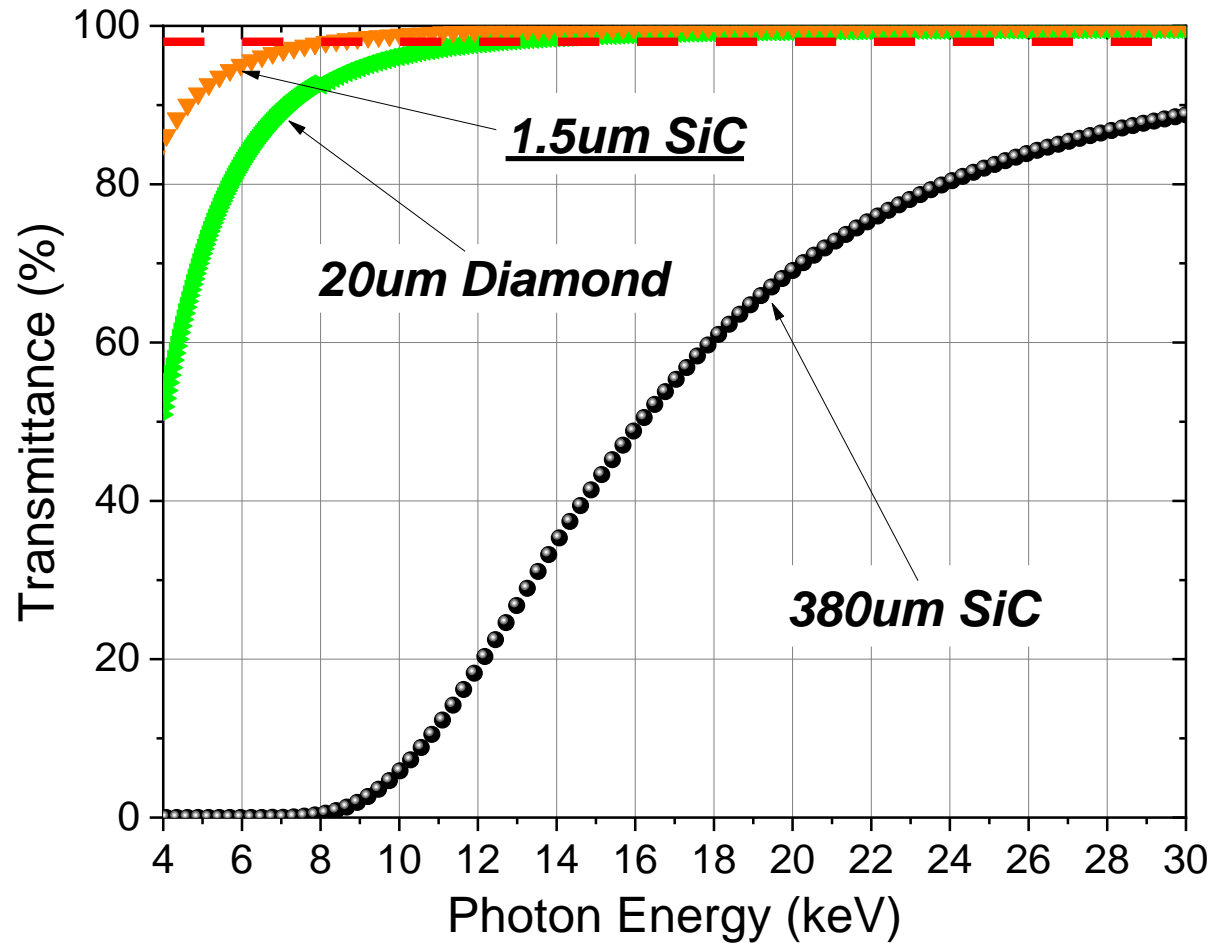
Best possible material for solid-state sensors



Best possible material for solid-state sensors

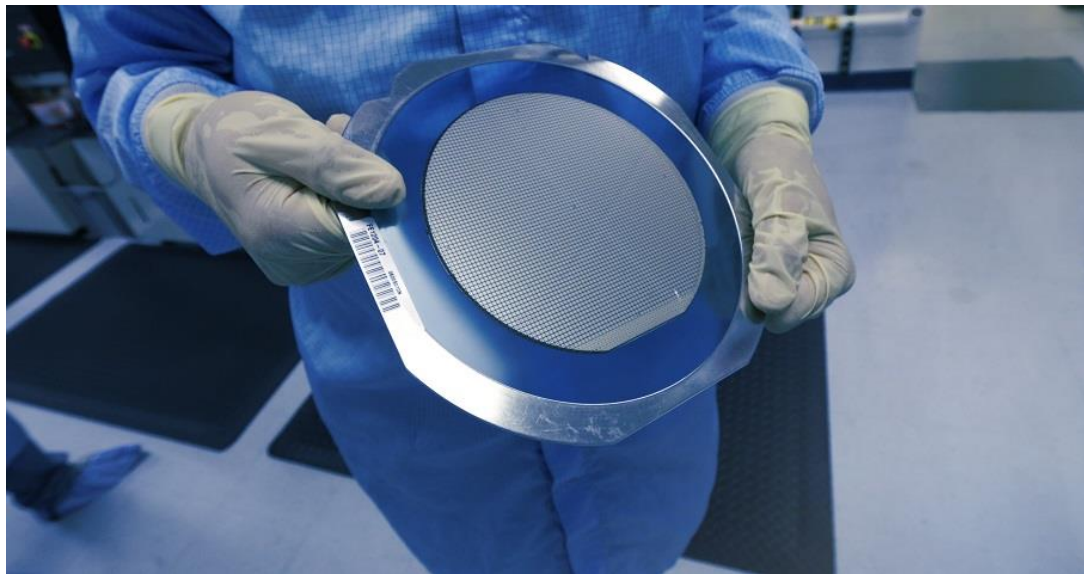


Best possible material for solid-state sensors



Best possible material for solid-state sensors

SILICON CARBIDE



<0.025% etching error needed! (on several mm²)

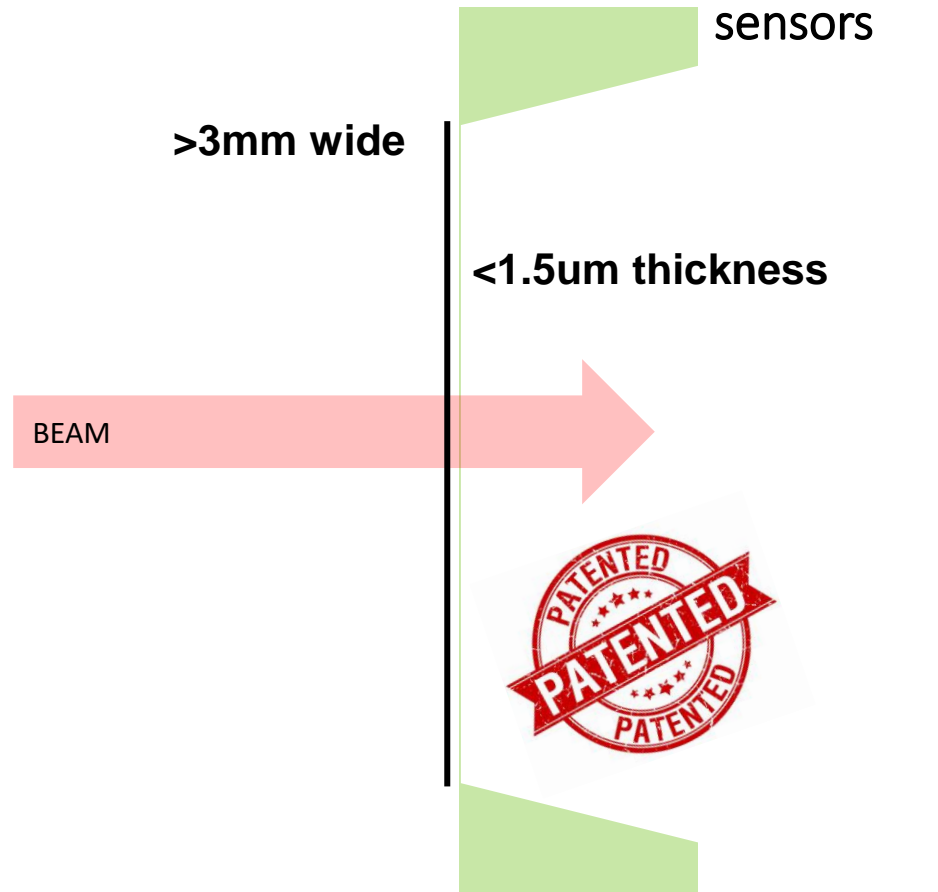
IMPOSSIBLE TO HANDLE!!

Best possible material for solid-state sensors

Free-standing sensors

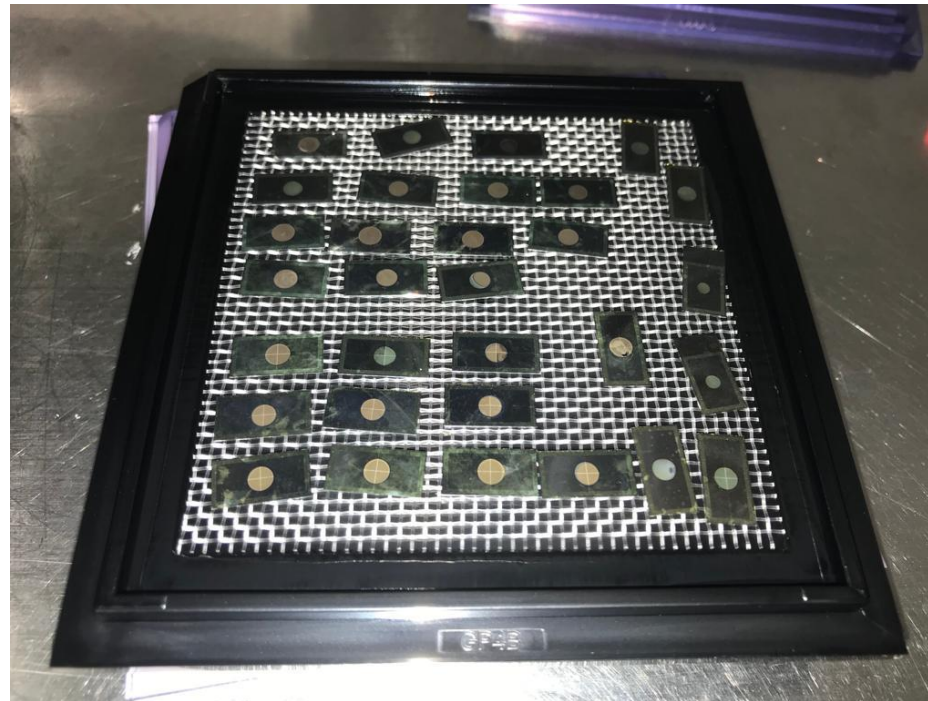


x.2 Patented thinning technology
more patents (x2) in pipeline



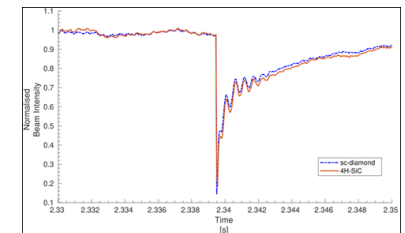
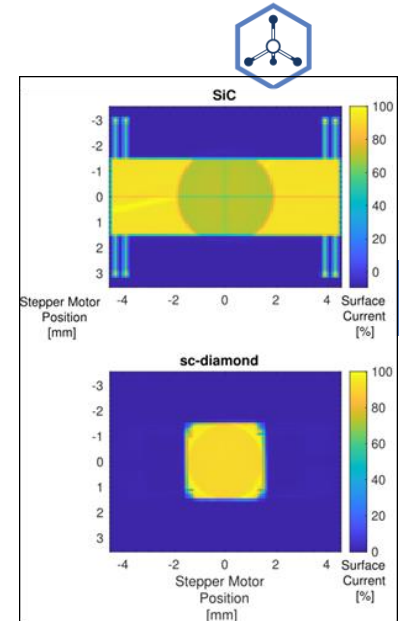
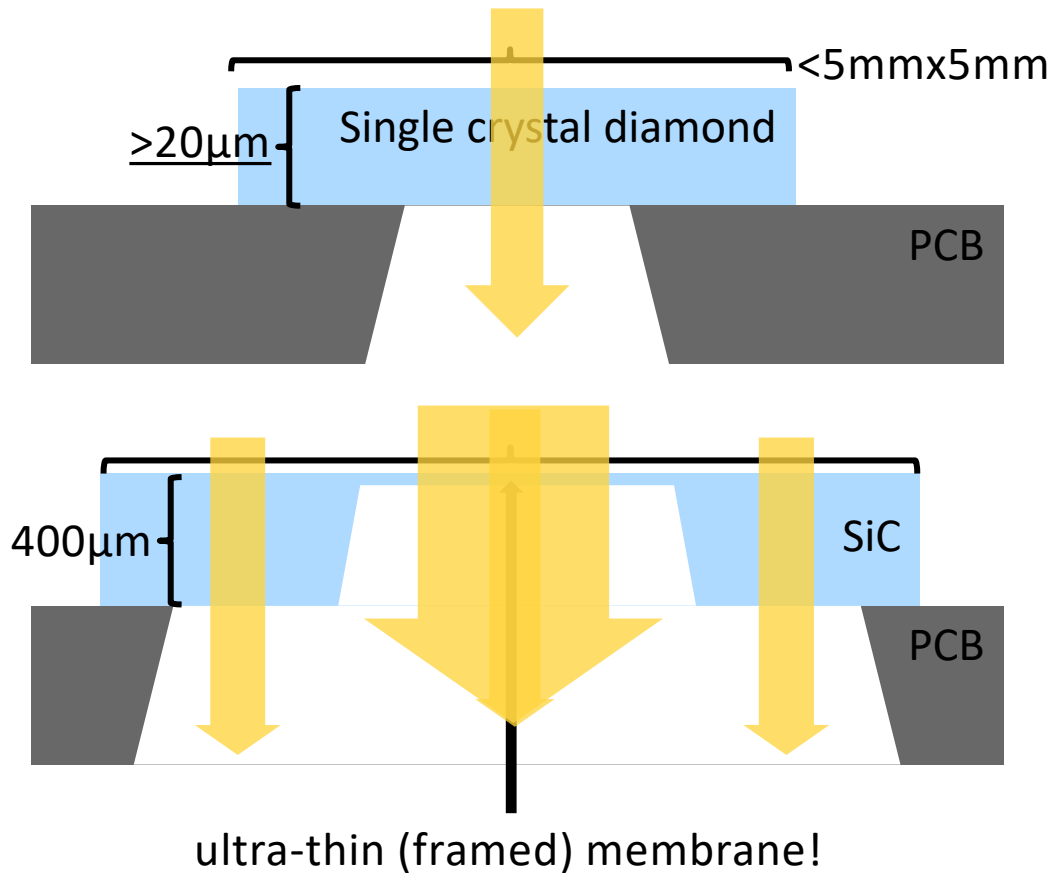
Best possible material for solid-state sensors

SILICON CARBIDE
FREE-STANDING MEMBRANES
INTENSITY AND POSITION MONITORS

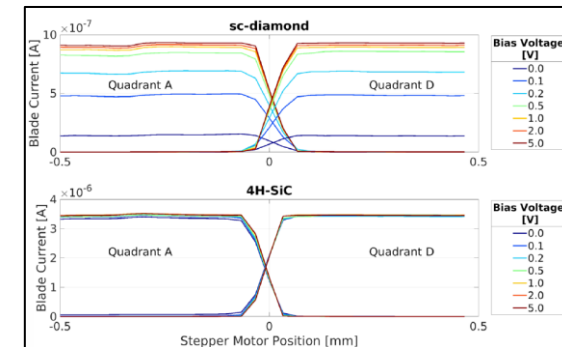


Diamond or Silicon Carbide?

“A direct experimental comparison of single-crystal CVD diamond and silicon carbide X-ray beam position monitors” *C. Houghton, JSR 30, 876 (2023)*

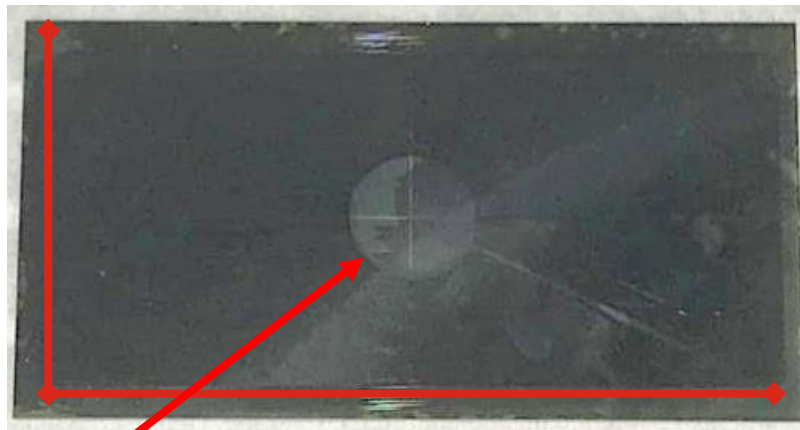


SenSiC



*up to instrumental limits

SILICON CARBIDE

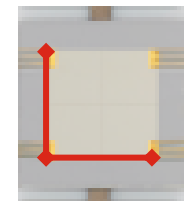


11 mm

23 mm

4 mm Ø

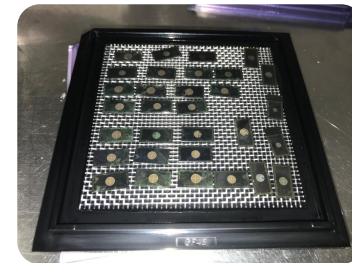
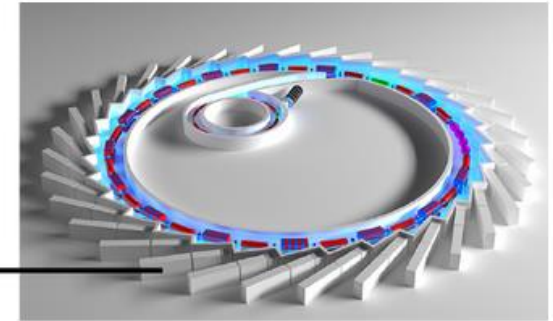
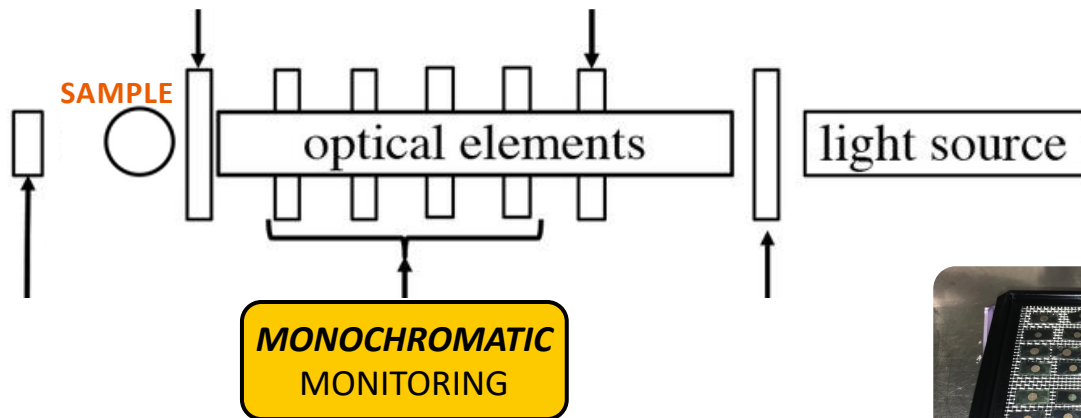
CVD DIAMOND



4 mm

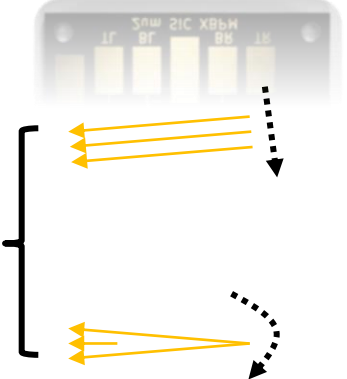
4 mm

Locations for in-line Synchrotron monitoring

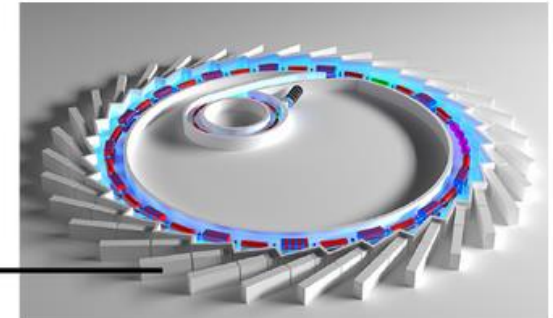
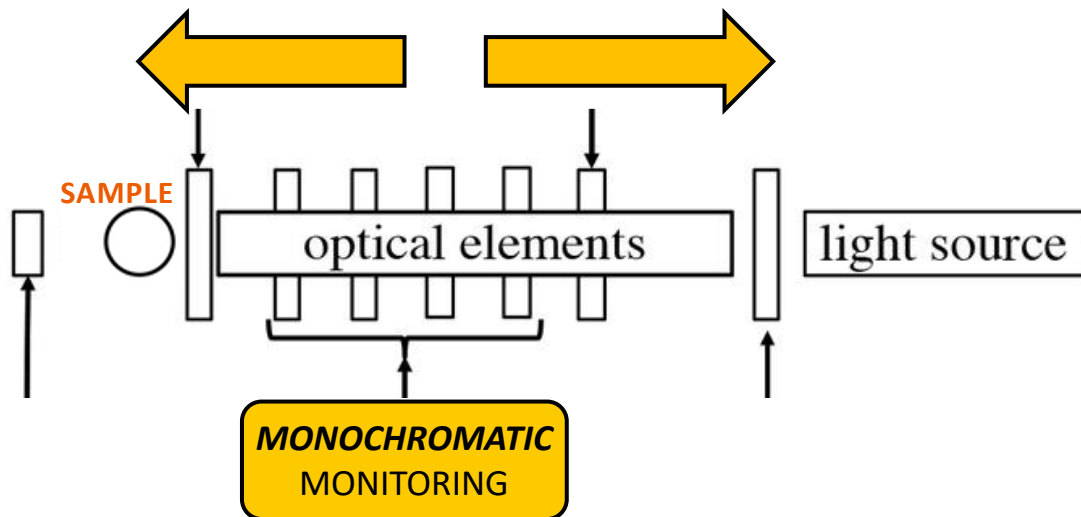


Commercially available XBPM

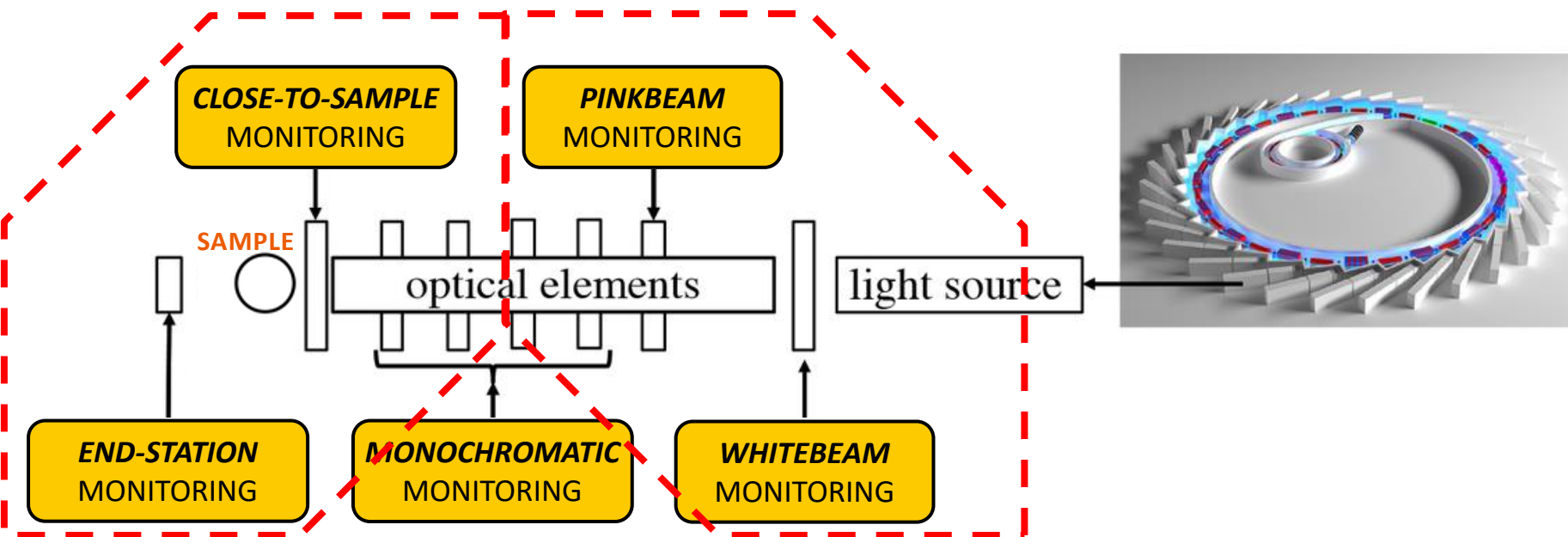
- 1) Monochromatic
- 2) *Hard-Xray*
- 3) *Position*
- 4) Only on *single-feedback* schema



Locations for in-line Synchrotron monitoring

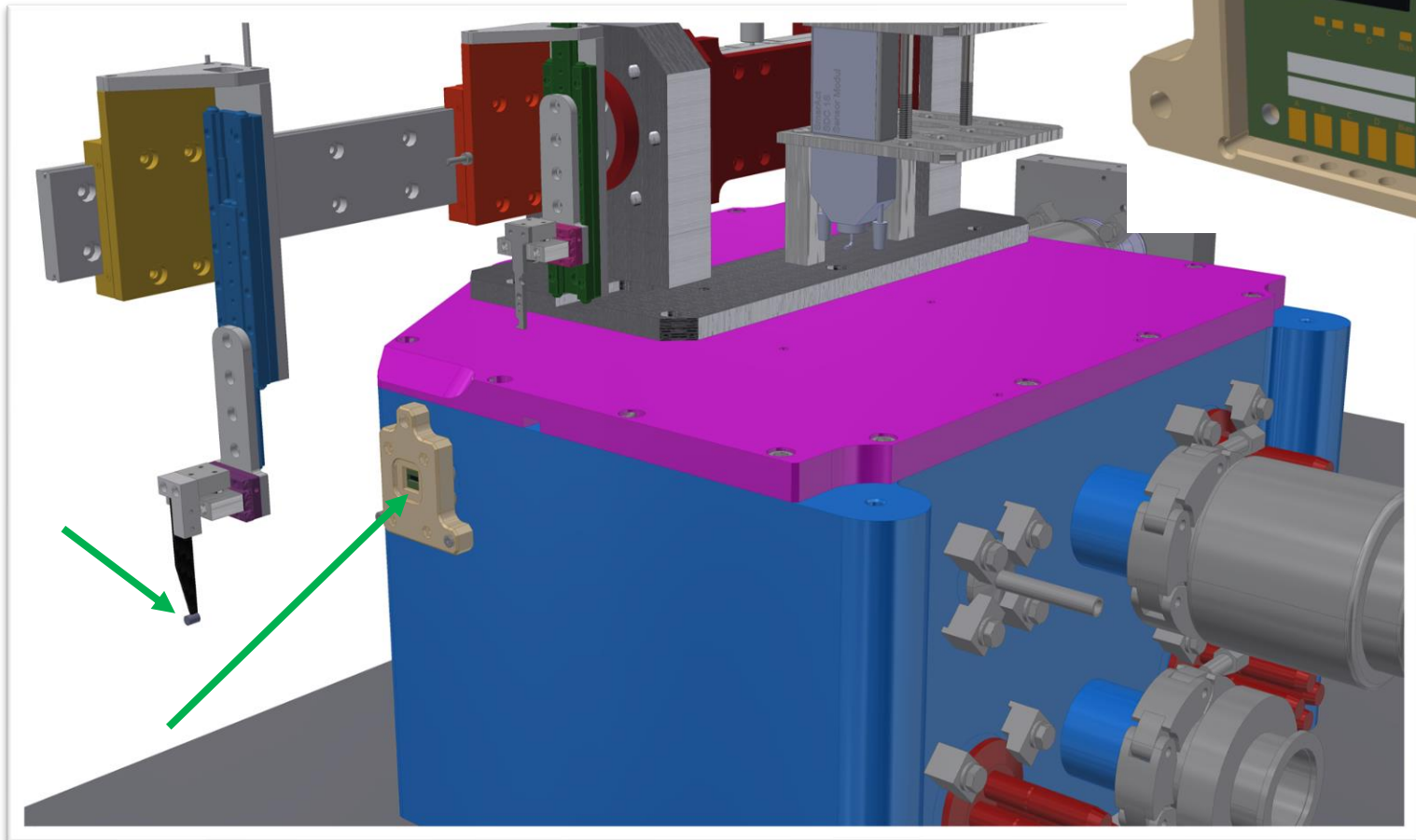


Locations for in-line Synchrotron monitoring



Near sample monitoring

-Fast/compact intensity sensor*



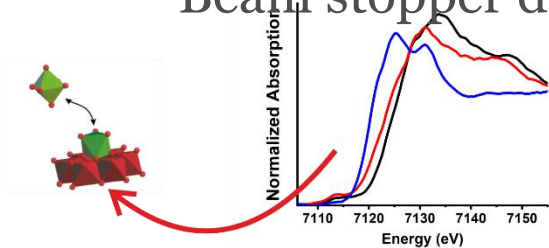
Near sample monitoring

-Fast/compact intensity sensor*



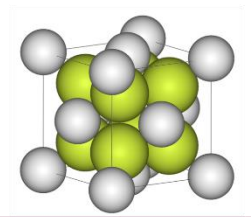
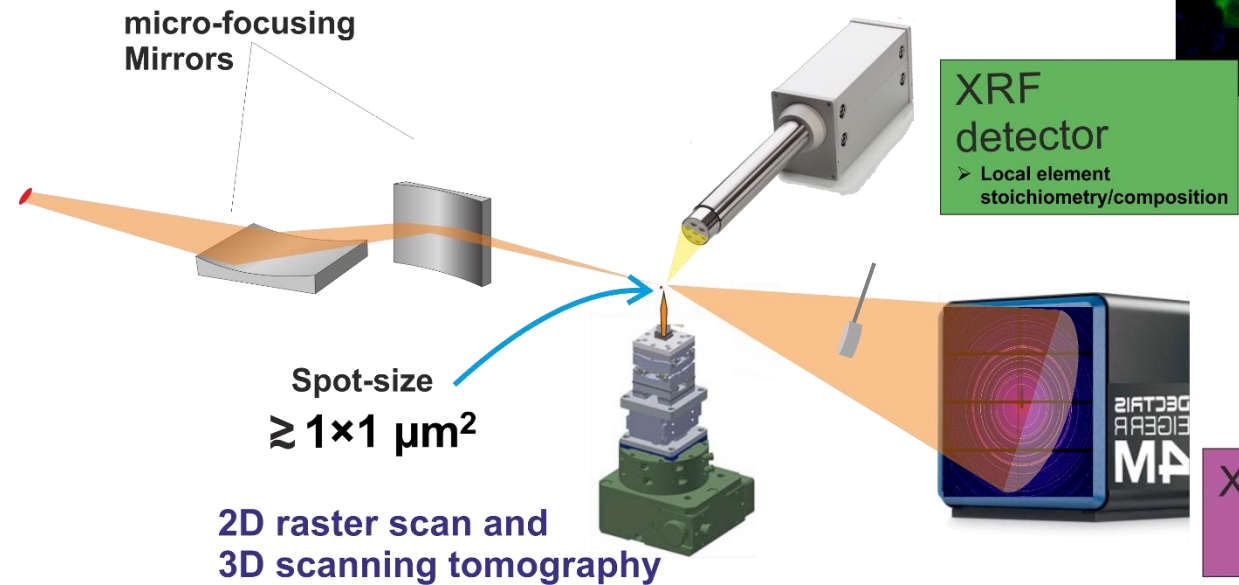
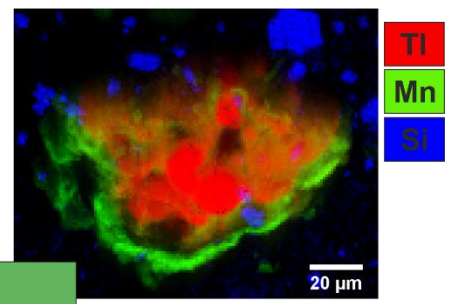
Near sample monitoring

-Beam stopper diode (no transmittance mode)



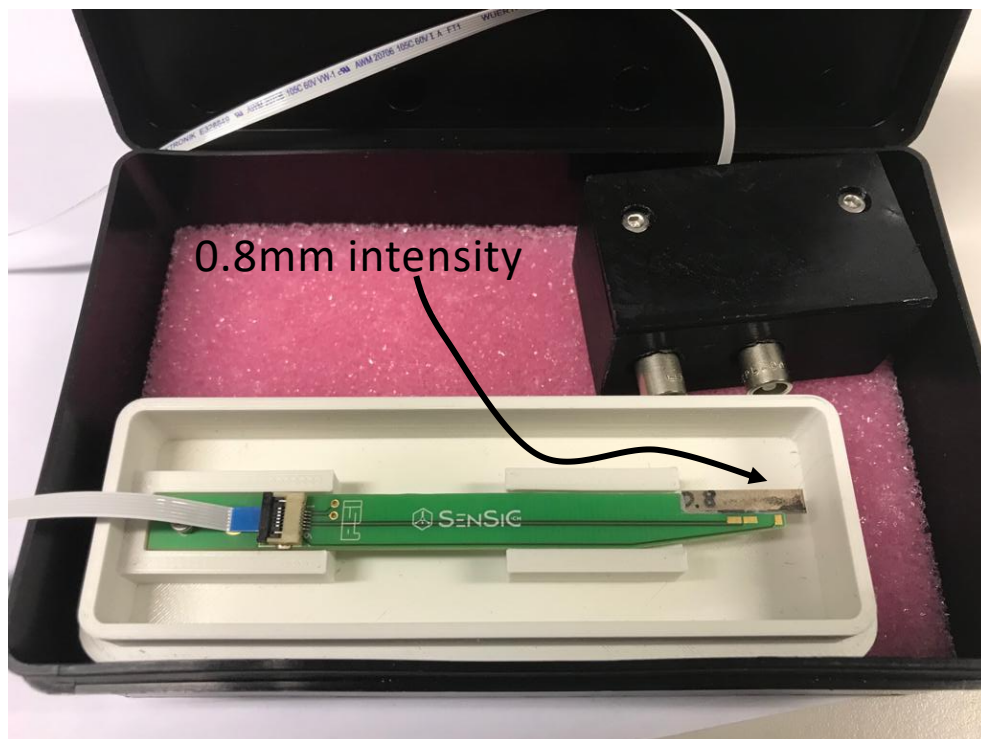
microscopic X-ray Absorption-Spectroscopies

- > Oxidation state
- > Chemical speciation
- > Local atomic coordination



Near sample monitoring

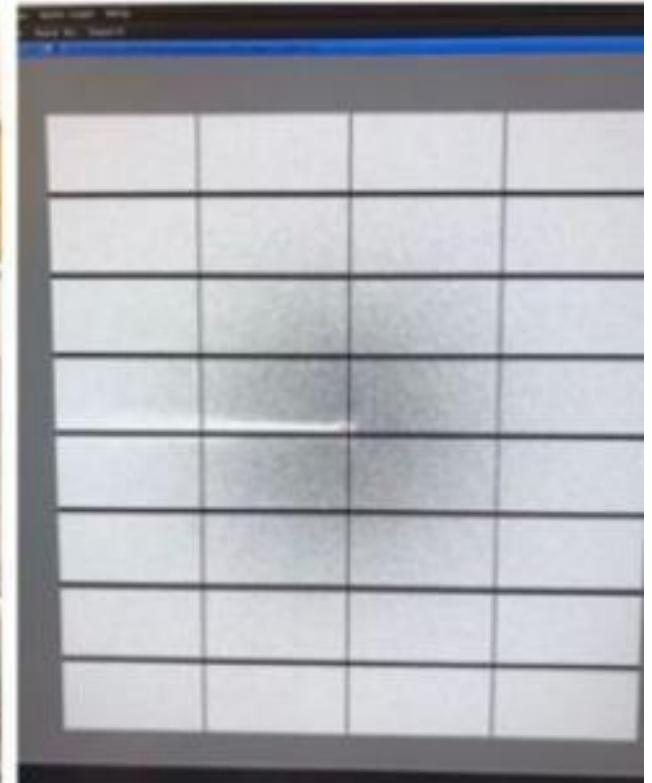
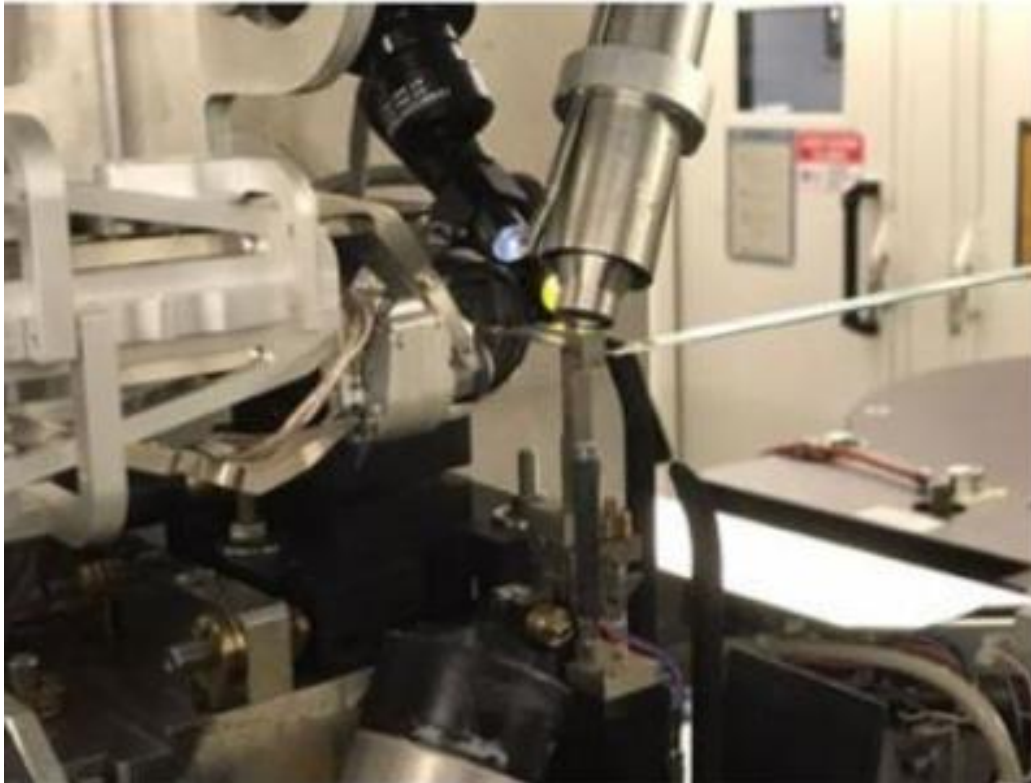
-Beam stopper diode (no transmittance mode)



*

Near sample monitoring

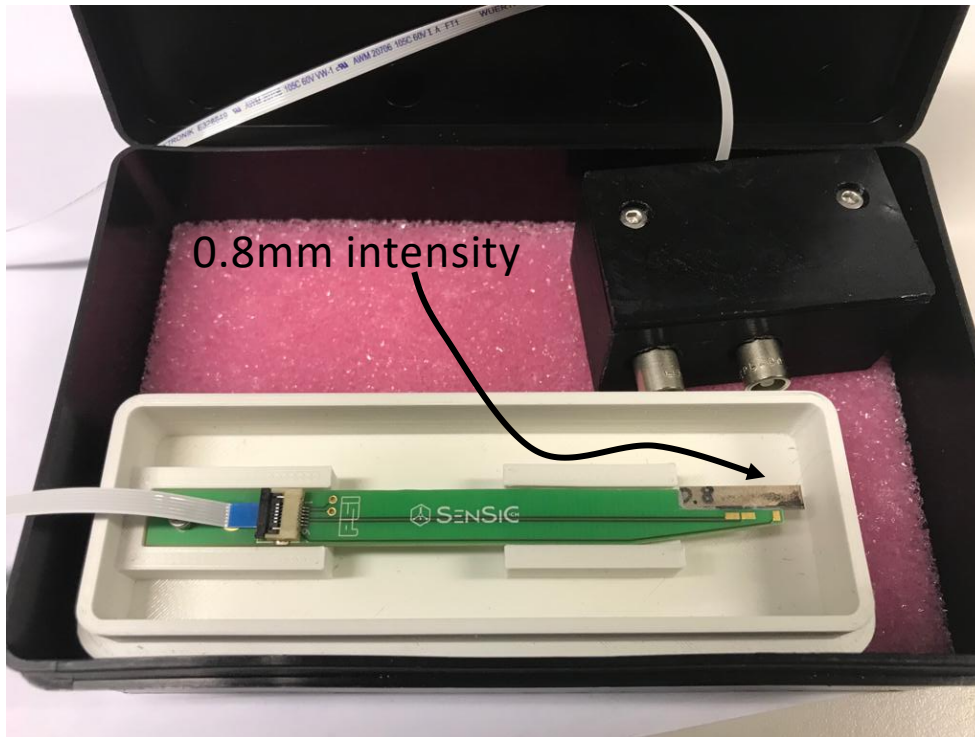
-Beam stopper diode (no transmittance mode)



*

Near sample monitoring

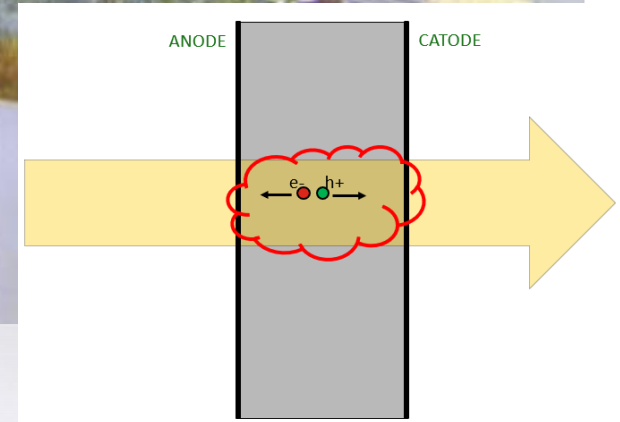
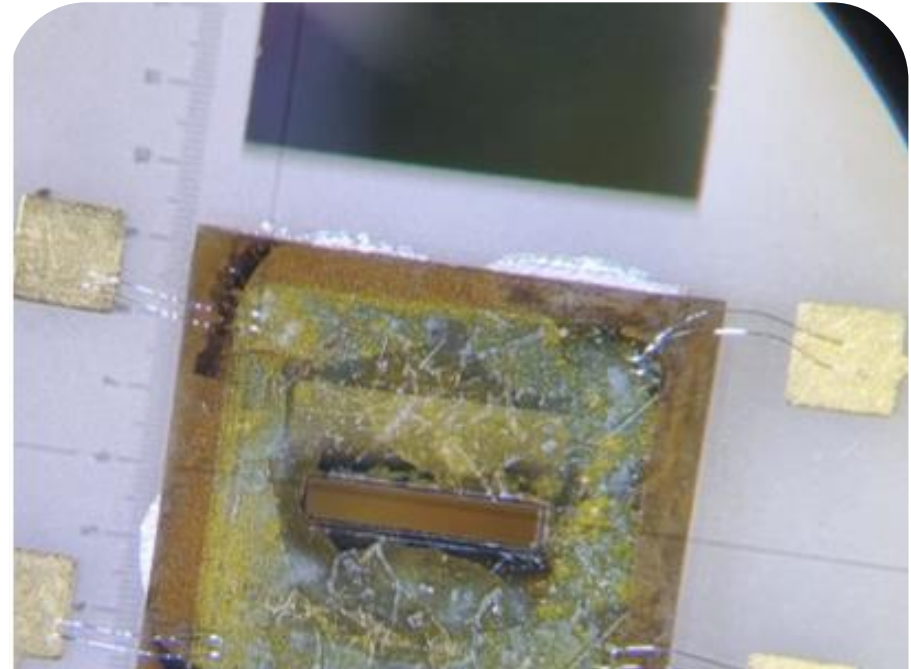
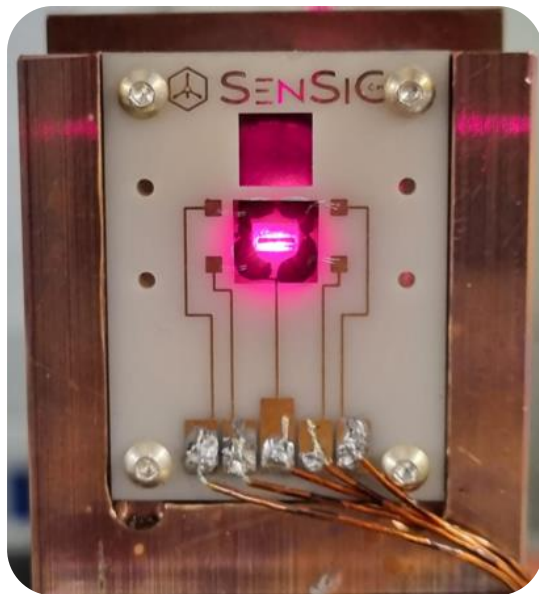
-Beam stopper diode (no transmittance mode)

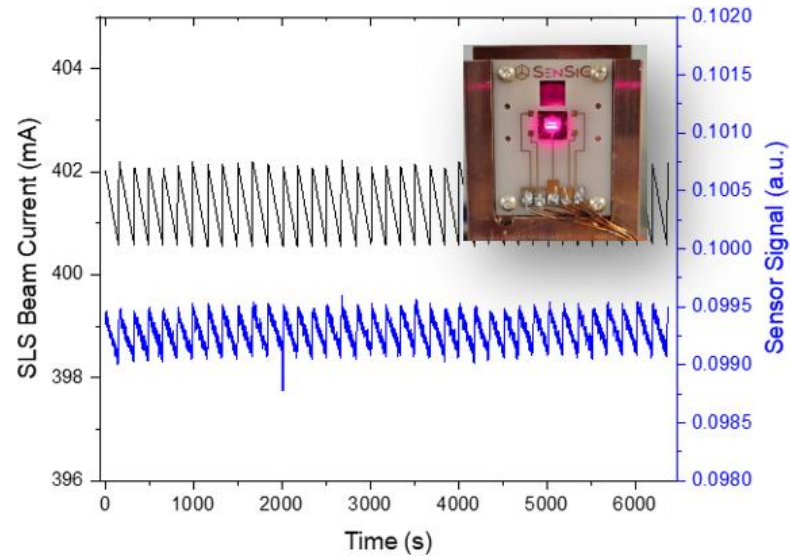
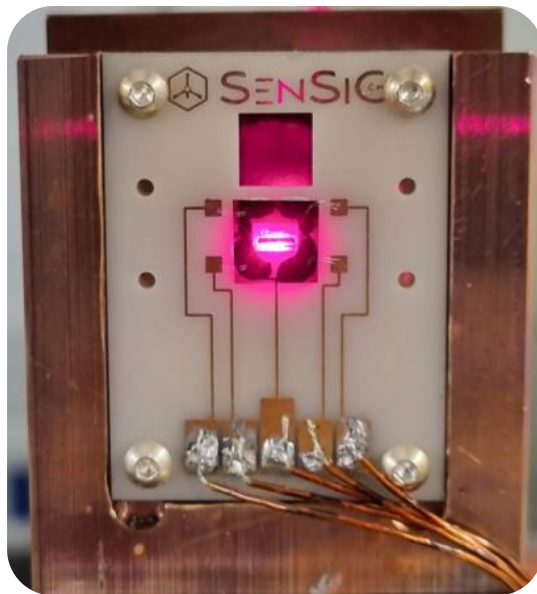


- 0.8mm intensity monitor
- 2mm intensity monitor
- 2mm position monitor
- 3mm position monitor

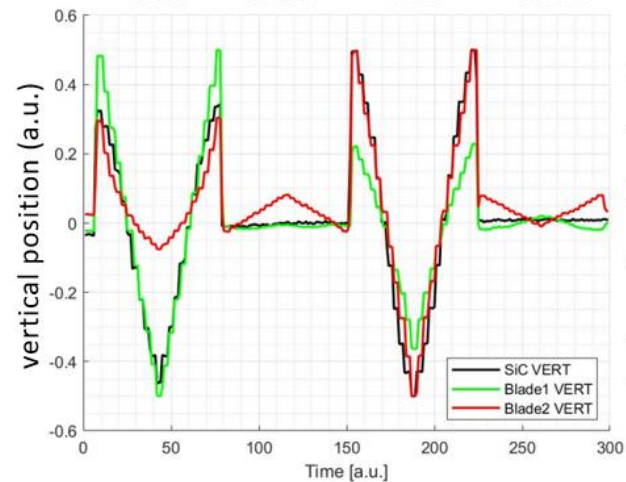


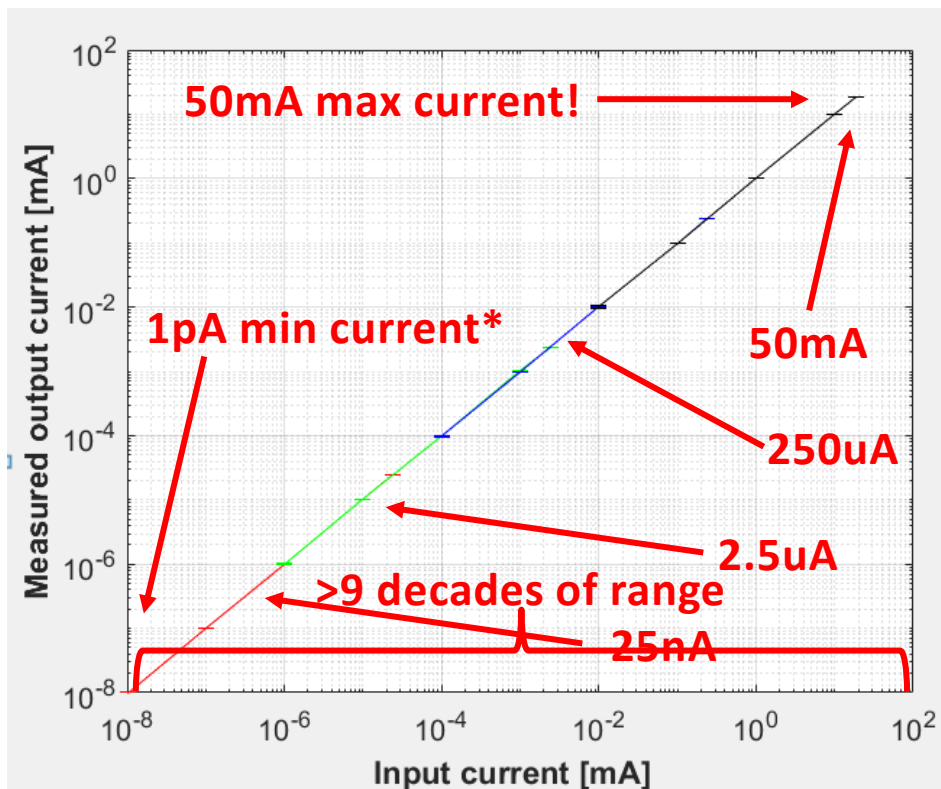
*



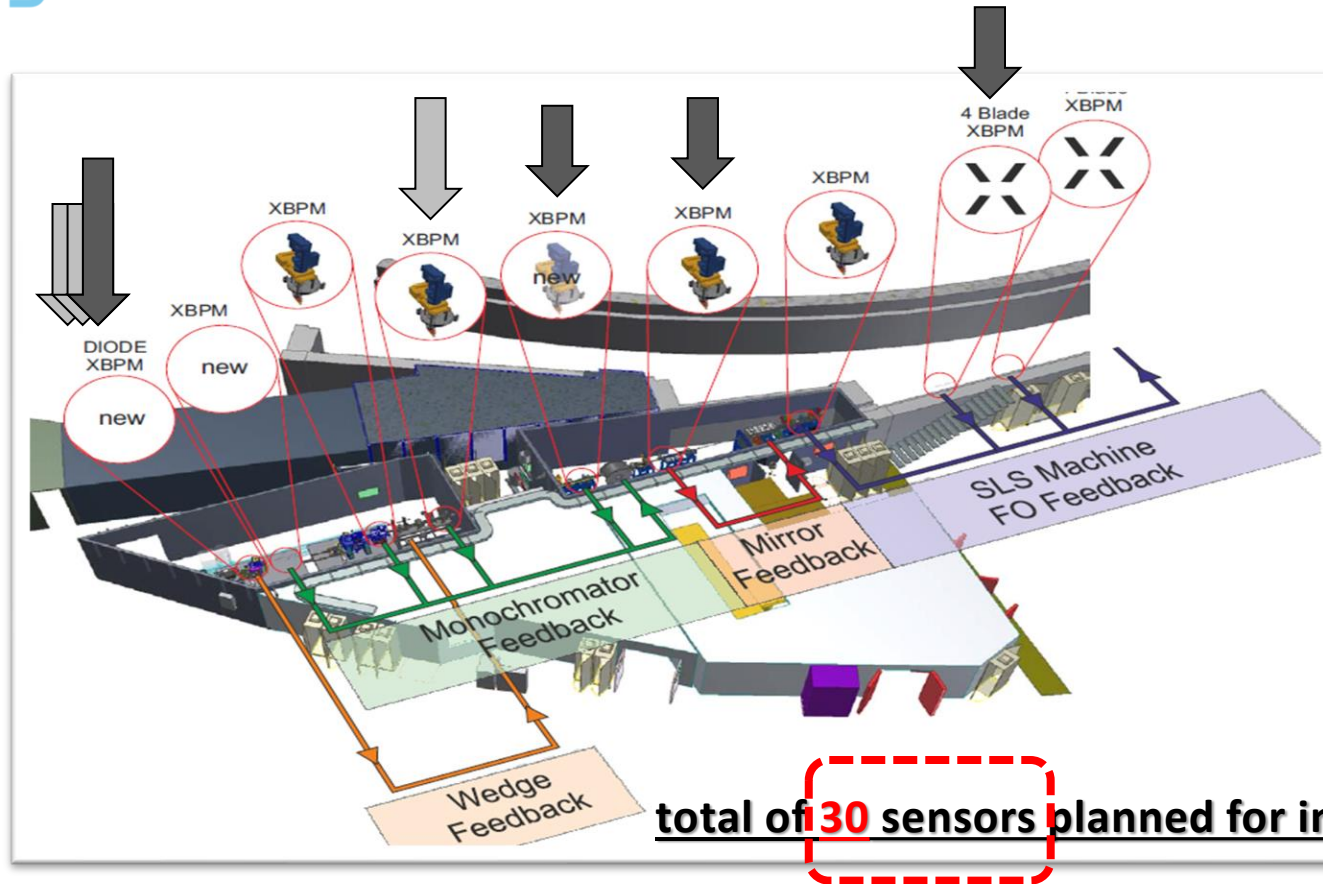


(angle) (angle) (position) (position)
 VERT HORIZ VERT HORIZ





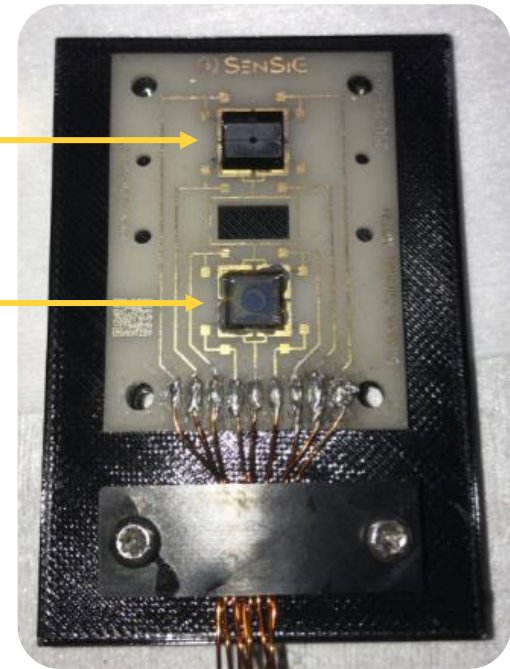
**EPICS (QuadEM) COMPATIBLE, WITH POSSIBILITY OF
MUTIPLEXING AMONG SENSORS**



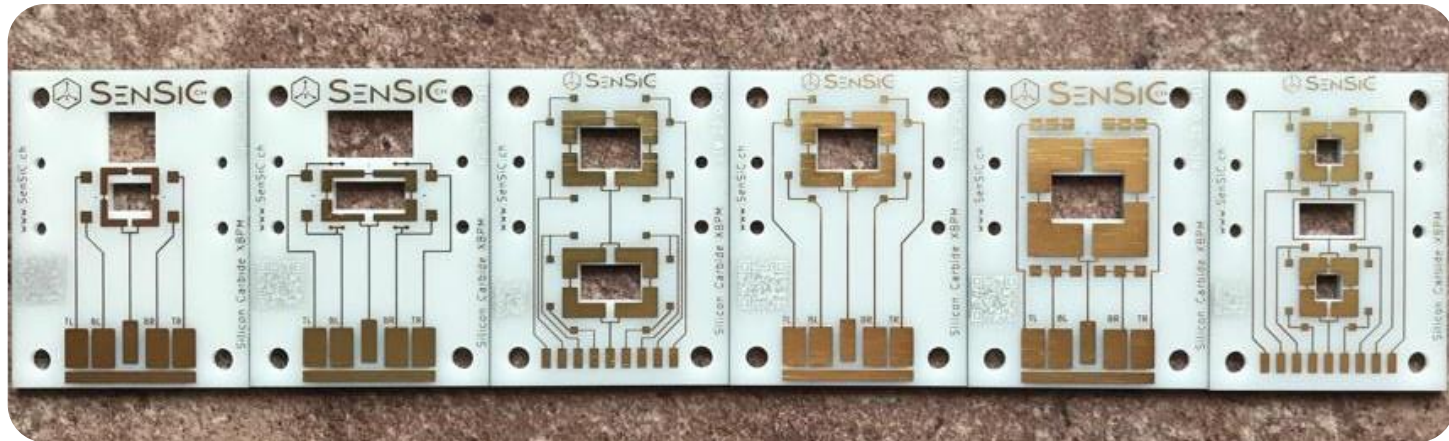
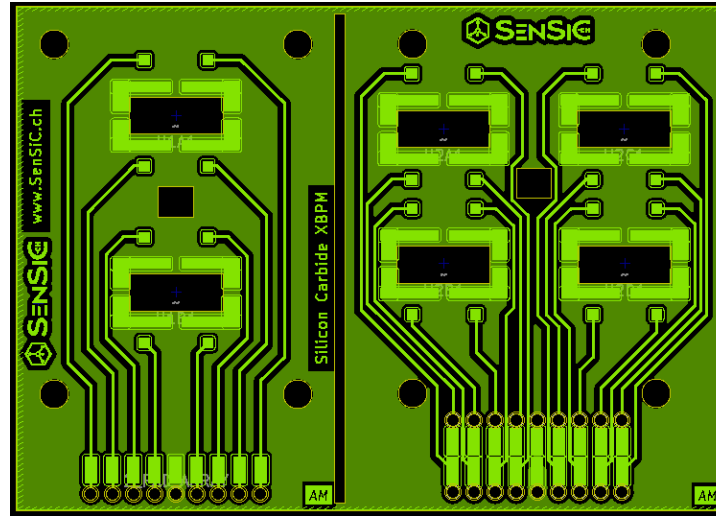
- **Currently installed:**
n.7 sensors (after mono, IO, nano-focus, pinkbeam and beam-stopper intensity)
- **Planned:** multiple pixelated, before mono, whitebeam, beam-stopper position

SENSOR FOR WHITE BEAM

SENSOR FOR MONOCHROMATIC BEAM

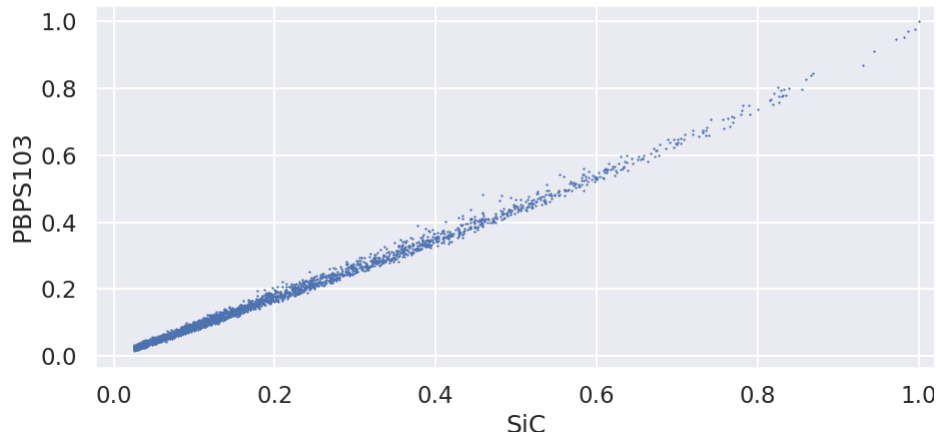


Multi-sensors packaging

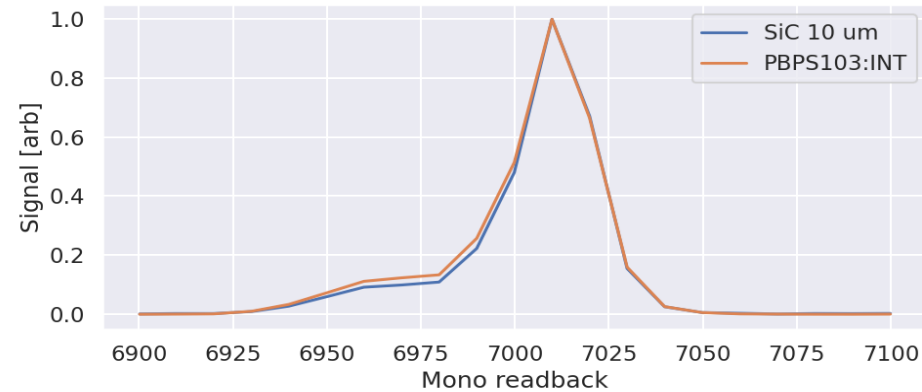


- 7 keV, PINKBEAM, 1 mJ/pulse

Correlation over mono scan



7 keV, 200 V bias



Huge signal level

- Needs attenuated mono beam
- 40 dB electrical signal attenuation (x100)
- Biasing increase from 40 - 200 V helps but nonlinearity observed

- **DEVELOPED INLINE MONITORS WITH GREATER POTENTIALITIES AND POSSIBILITIES THAN DIAMOND BASED ONES**
- **CONSOLIDATED PRODUCTS : MONOCHROMATIC, INTENSITY/POSITION, MONITORS 1.5um**
- **NEW PRODUCTS: POLYCHROMATIC, INTENSITY/POSITION, MONITORS**
- **NEW PRODUCTS: BEAMSTOPPERS, INTENSITY/POSITION, OF DIFFERENT SIZES (<0.8mm)**
- **NEW PRODUCTS: READOUT SYSTEMS (EPICS COMPATIBLE) WITH VERY LARGE DYNAMIC RANGES (UP TO 50mA)**
- **DEVELOPING MULTY-CHIP SENSORS (X2). (X3-X4 IN PROGRESS)**
- **FIRST PROMISING TEST AT XFEL**

COLLABORATION WITH FMB-OXFORD

